

isc Silicon NPN Power Transistor

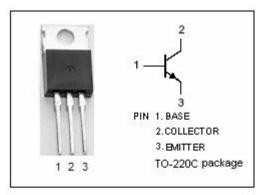
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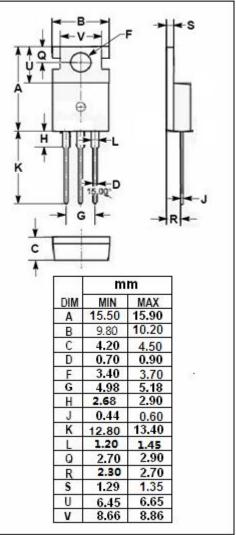
DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V_{CEO(SUS)}= 80V(Min.)
- Collector-Emitter Saturation Voltage-
- : V_{CE(sat)}= 1.6V(Max.) @I_C= 5A
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for power amplifier applications.





ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOLPARAMETERVALUEUNITVCBOCollector-Base Voltage150VVCESCollector-Emitter Voltage150VVCEOCollector-Emitter Voltage80VVEBOEmitter-Base Voltage6VIcCollector Current-Continuous5AICMCollector Current-Peak10A				
VCES Collector-Emitter Voltage 150 V VCEO Collector-Emitter Voltage 80 V VEBO Emitter-Base Voltage 6 V Ic Collector Current-Continuous 5 A	STMBOL	PARAMETER	VALUE	UNIT
V _{CEO} Collector-Emitter Voltage 80 V V _{EBO} Emitter-Base Voltage 6 V Ic Collector Current-Continuous 5 A	V _{CBO}	Collector-Base Voltage	150	v
V _{EBO} Emitter-Base Voltage 6 V Ic Collector Current-Continuous 5 A	VCES	Collector-Emitter Voltage	150	V
Ic Collector Current-Continuous 5 A	V _{CEO}	Collector-Emitter Voltage	80	V
	V _{EBO}	Emitter-Base Voltage	6	V
I _{CM} Collector Current-Peak 10 A	lc	Collector Current-Continuous	5	A
	I _{CM}	Collector Current-Peak	10	A
$ P_{C} \qquad \begin{array}{c} Collector \ Power \ Dissipation \\ @ \ T_{C} = 25 \ C \end{array} \qquad \begin{array}{c} 40 \qquad W \end{array} $	Pc		40	W
T _J Junction Temperature 150 °C	TJ	Junction Temperature	150	°C
Tstg Storage Temperature Range -55~150 °C	T _{stg}	Storage Temperature Range	-55~150	°C

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ELECTRICAL CHARACTERISTICS

$T_{c}\text{=}25^{\circ}\!\!\!\!\!\!C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 30mA; L= 25mH	80			V
V(BR)EBO	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			1.6	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 5A; V _{CE} = 4V			1.5	V
Ісво	Collector Cutoff Current	V _{CB} = 150V; I _E = 0			1	mA
h _{FE}	DC Current Gain	I _C = 5A; V _{CE} = 4V	14			
f⊤	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 10V		40		MHz
t _f	Fall Time	I _C = 5A, I _{B1} = 0.8A; V _{EB} = 5V			1	μ S

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